

Silicon PNP Power Transistors

BD234 BD236 BD238

DESCRIPTION

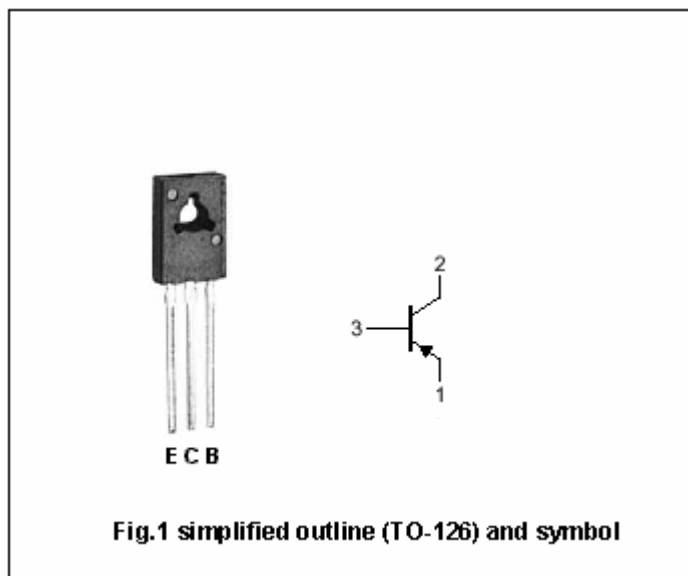
- With TO-126 package
- Complement to type BD233/235 /237

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BD234	Open emitter	-45	V
		BD236		-60	
		BD238		-100	
V_{CEO}	Collector-emitter voltage	BD234	Open base	-45	V
		BD236		-60	
		BD238		-80	
V_{EBO}	Emitter -base voltage		Open collector	-5	V
I_C	Collector current (DC)			-2	A
I_{CM}	Collector current-Peak			-6	A
P_C	Collector power dissipation		$T_C=25^{\circ}\text{C}$	25	W
T_j	Junction temperature			150	$^{\circ}\text{C}$
T_{stg}	Storage temperature			-65~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage		I _C =-1A; I _B =-0.1A			-0.6	V
V _{BE}	Base-emitter on voltage		I _C =-1A; V _{CE} =-2V			-1.3	V
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BD234	I _C =-0.1A; I _B =0	-45			V
		BD236		-60			
		BD238		-80			
I _{CBO}	Collector cut-off current	BD234	V _{CB} =-45V; I _E =0			-100	μA
		BD236	V _{CB} =-60V; I _E =0				
		BD238	V _{CB} =-100V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-1	mA
h _{FE-1}	DC current gain		I _C =-150mA; V _{CE} =-2V	40			
h _{FE-2}	DC current gain		I _C =-1A; V _{CE} =-2V	25			
f _T	Transition frequency		I _C =-250mA; V _{CE} =-10V	3			MHz

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PACKAGE OUTLINE

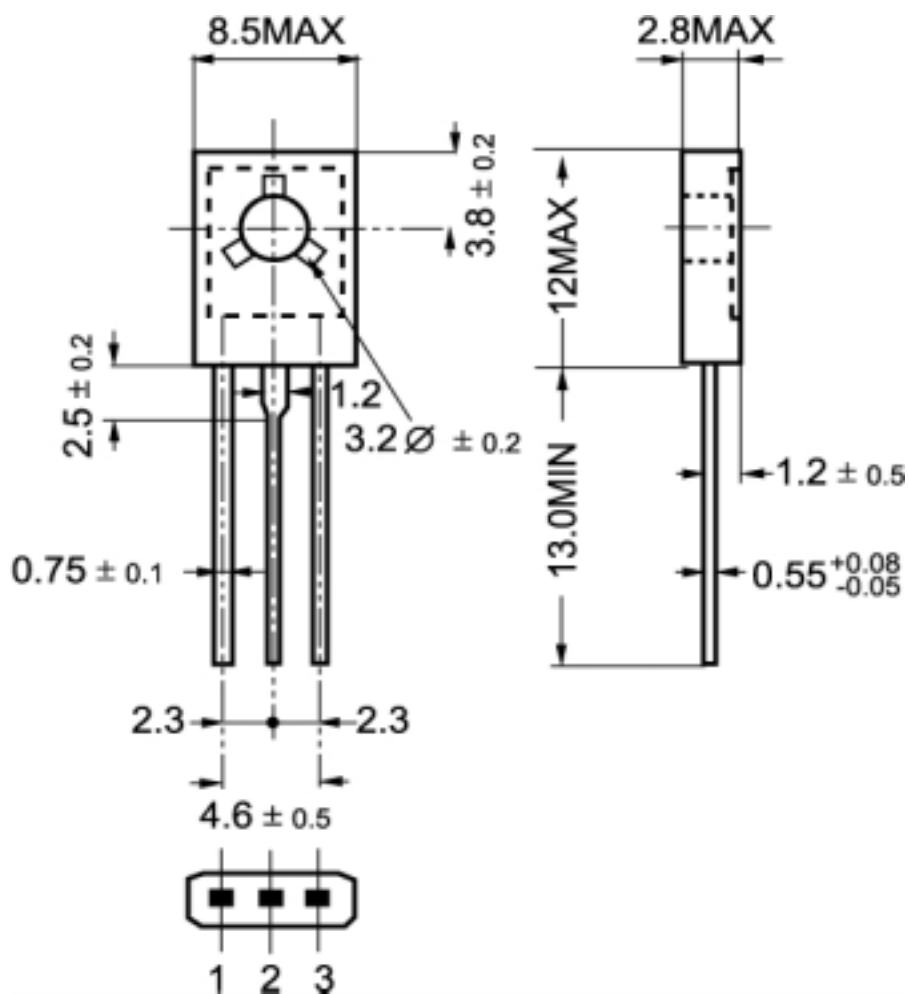


Fig.2 Outline dimensions